

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 30	0.0085 at $V_{GS} = -10$ V	- 14
	0.014 at $V_{GS} = -4.5$ V	- 11

FEATURES

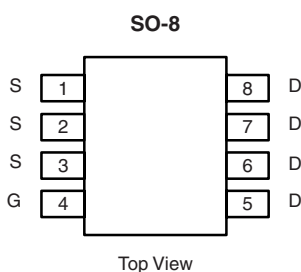
- TrenchFET® Power MOSFET
- ESD Protection: 3000 V



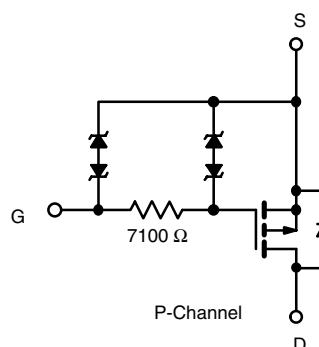
RoHS
COMPLIANT

APPLICATIONS

- Notebook PC
 - Load Switch
 - Adapter Switch



Ordering Information: Si4483EDY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	10 sec	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 30		V
Gate-Source Voltage	V_{GS}	± 25		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	- 14	- 10	A
		- 11	- 8	
Pulsed Drain Current	I_{DM}	- 50		
Continuous Source Current (Diode Conduction) ^a	I_S	- 2.7	- 1.36	
Maximum Power Dissipation ^a	P_D	3.0	1.5	W
		1.9	0.95	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	33	42	$^\circ\text{C/W}$
		70	85	
Maximum Junction-to-Foot (Drain)	R_{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

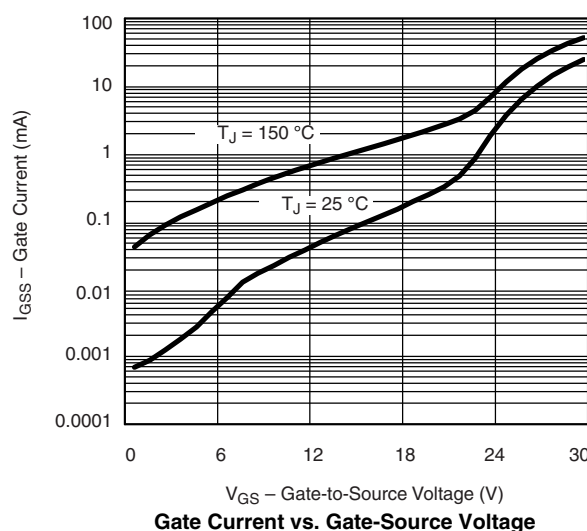
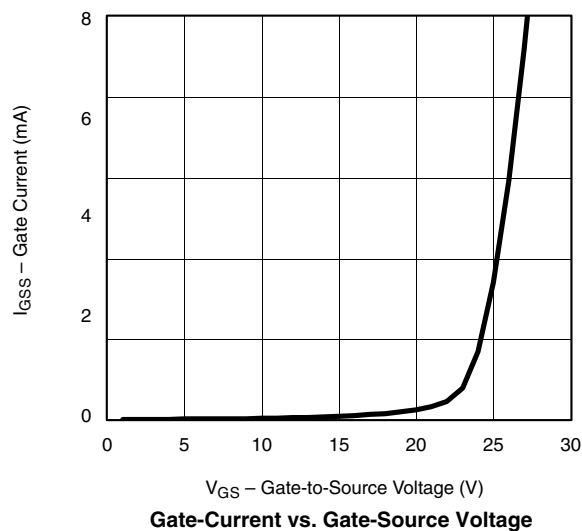
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 4.5\text{ V}$			± 1	μA
		$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 10	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 70\text{ }^{\circ}\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -10\text{ V}$	- 30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -14\text{ A}$		0.007	0.0085	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -11\text{ A}$		0.0115	0.014	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -14\text{ A}$		60		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -2.7\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.74	- 1.1	V
Dynamic^b						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$, $R_L = 15\text{ }\Omega$ $I_D = -1\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 6\text{ }\Omega$		10	15	μs
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			42	65	
Fall Time	t_f			50	80	

Notes:

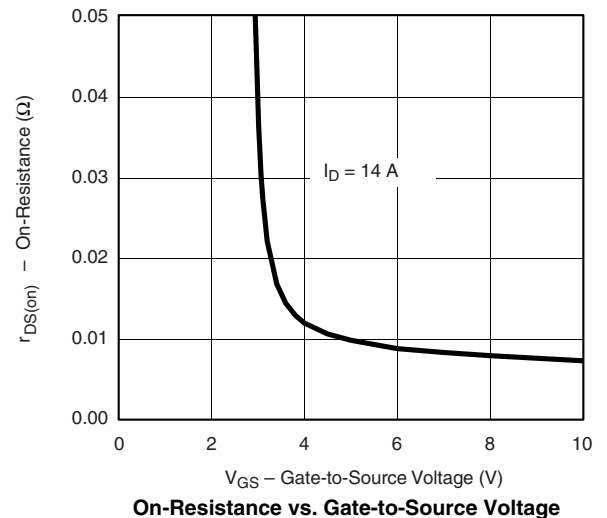
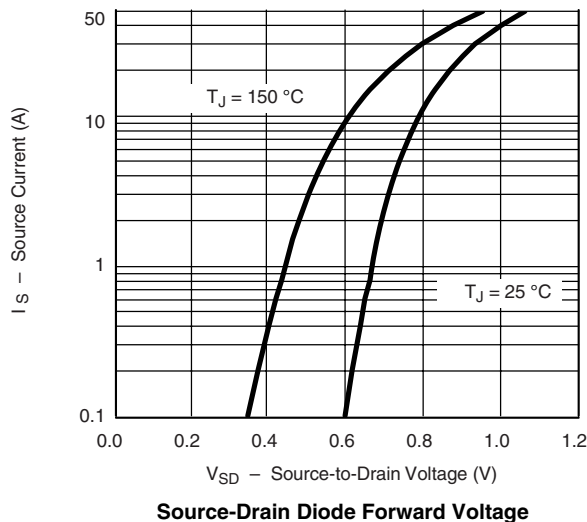
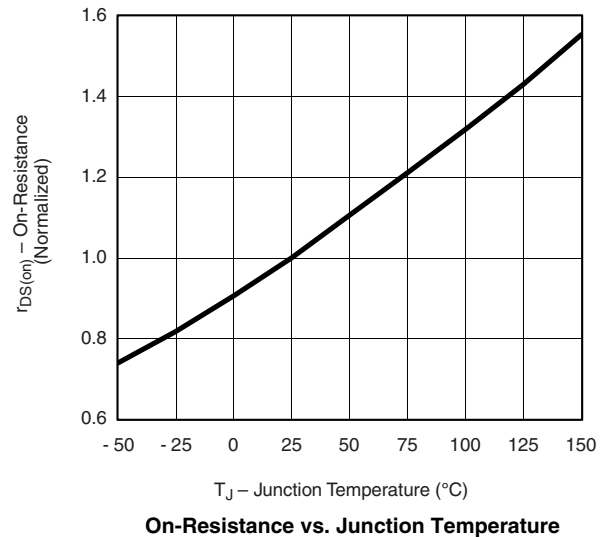
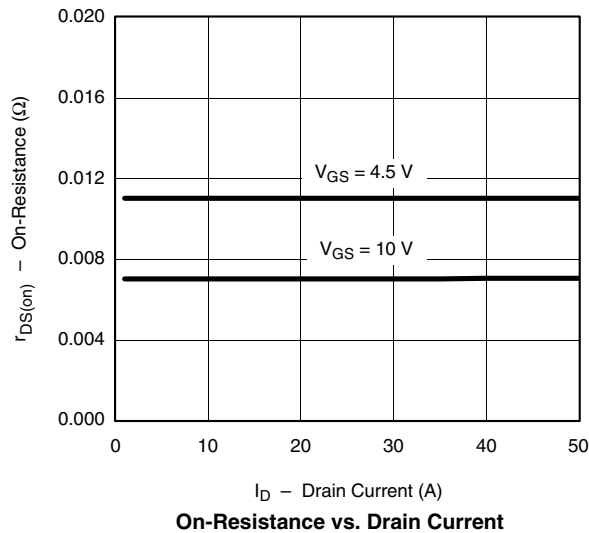
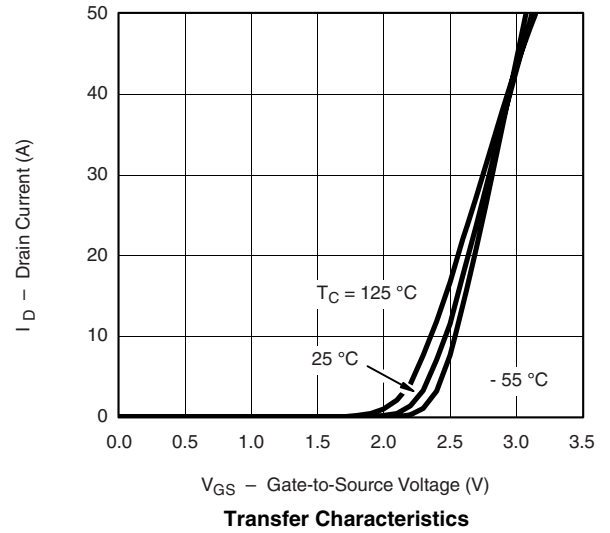
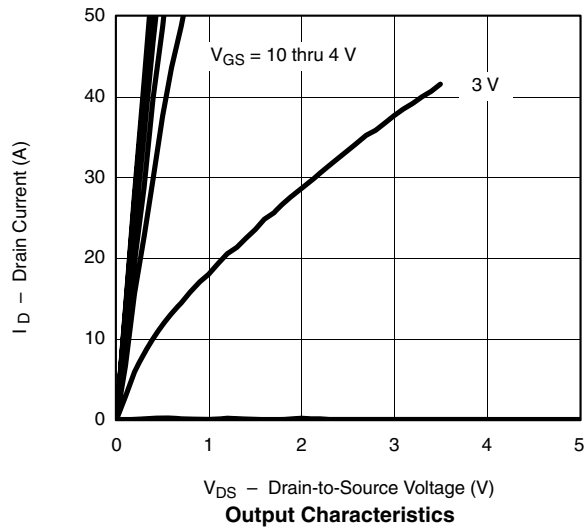
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

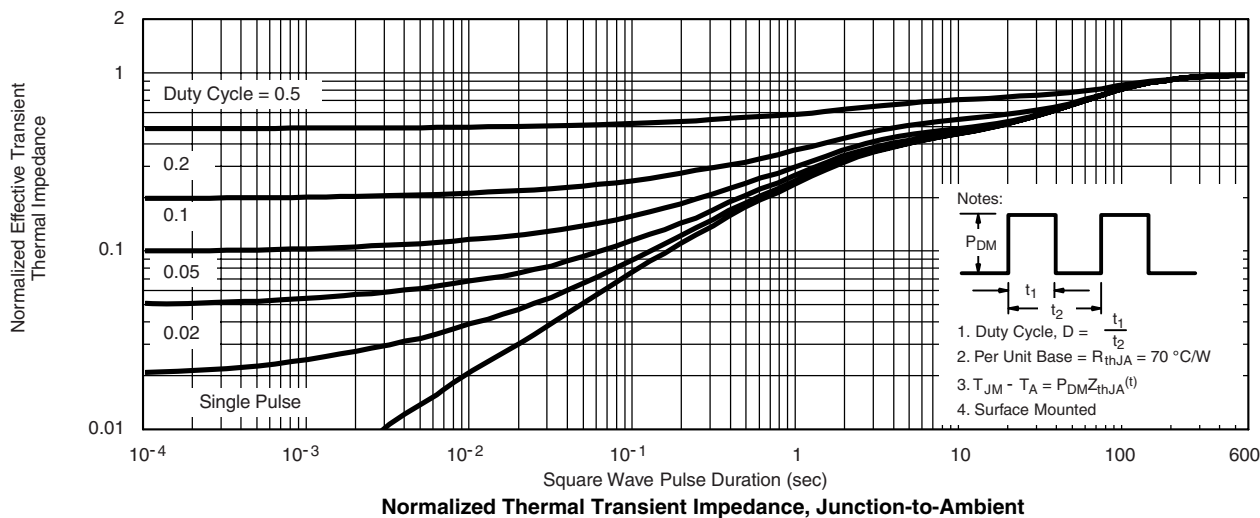
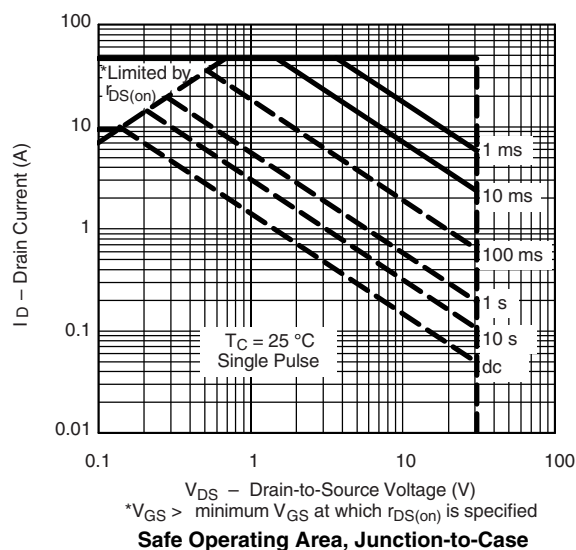
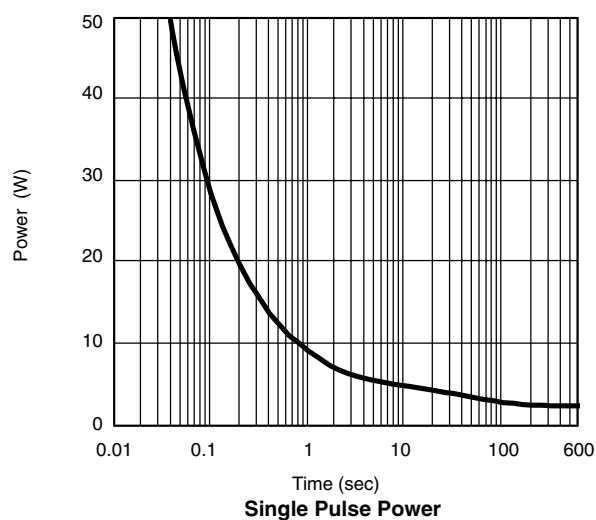
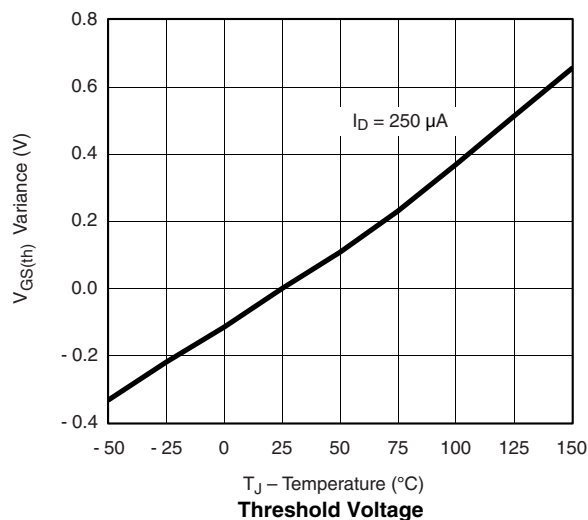
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

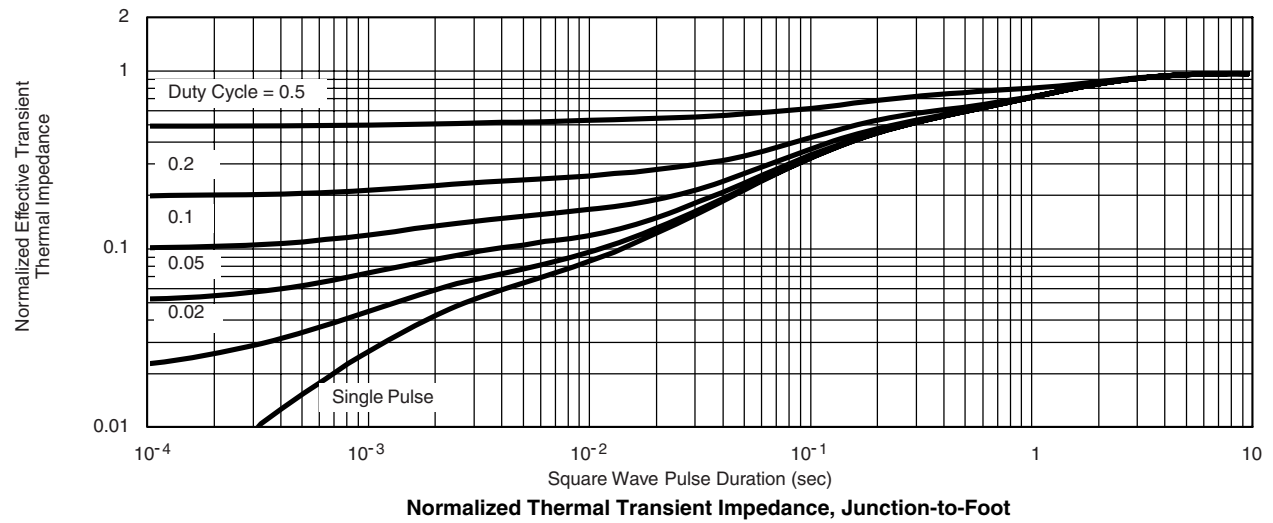
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